

CXA2550M/N

RF Amplifier for CD Players

Description

The CXA2550M/N is an IC developed for compact disc players. This IC incorporates an RF amplifier, focus error amplifier, tracking error amplifier, APC circuit and RF level control circuit. (The voltageconverted optical pickup output is supported.)

Features

- Low power consumption (35mW at 3.5V)
- APC circuit
- RF level control circuit
- Both single power supply and dual power supply operations possible.

Structure

Bipolar silicon monolithic IC

Applications

Compact disc players

Block Diagram and Pin Configuration (Top View)



Absolute Maximum Ratings (Ta = 25°C)

 Supply voltage 	Vcc		12	V
Operating temperature	Topr	-2	0 to +75	°C
 Storage temperature 	Tstg	-65	5 to +150	°C
Allowable power dissipa	ation			
	PD (SC	DP)	620	mW
	(SS	SOP)	370	mW

Operating Conditions

Supply voltage	Vcc – Vee	3.0 to 4.0	V



Sony reserves the right to change products and specifications without prior notice. This information does not convey any license by any implication or otherwise under any patents or other right. Application circuits shown, if any, are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits.

Pin Description

Pin No.	Symbol	I/O	Equivalent circuit	Description
1	AGCVTH		147 147 13.4k ≤ ↓ 10µ	Reference level variable pin for RF level control. The reference level can be varied by the external resistor.
2	LD	0		APC amplifier output pin.
3	PD	I	3 + 47 + 420 + 4	APC amplifier input pin.
4 5	PD1 PD2	1		Inversion input pin for RF I-V amplifiers. Connect these pins to the photodiodes A + C and B + D respectively. The current is supplied.
6	Vee		6 VEE	VEE pin.

Pin No.	Symbol	I/O	Equivalent circuit	Description
7 8	F E	I	$7 + 12p$ $260k$ $7 + 10\mu$ $8 + 10\mu$	Inversion input pin for F and E I-V amplifiers. Connect these pins to the photodiodes F and E respectively. The current is supplied.
9	EI		 ↓ ↓	Gain adjustment pin for I-V amplifier.
10	VC	ο	Vcc Vcc \downarrow 10 10 120 120 15k 120 15k 16k Vee	DC voltage output pin of (Vcc + VEE)/2. Connect to GND for ±1.75 power supply; connect a smoothing capacitor for single +3.5V power supply.
11	TE	ο		Tracking error amplifier output pin. E-F signal is output.

Pin No.	Symbol	I/O	Equivalent circuit	Description
12	FE_BIAS	I	$\begin{array}{c} 32k \\ 12 \\ 12 \\ 12 \\ 24p \\ 174k \\ 10\mu \end{array}$	Bias adjustment pin for inverted side of focus error amplifier.
13	FE	0	(13) (13)	Focus error amplifier output pin.
14	RFM	I	$ \begin{array}{c} 2k \\ 2k \\ 2k \\ 147 \\ 147 \\ 147 \\ 147 \\ 1m \\ 850 \\ 850 \\ 1m \\ 850 \end{array} $	RF amplifier inverted side input pin. RF amplifier gain is determined by the resistor connected between this pin and RFO pin.
15	RF O	ο	147 15 60k ≶ ↓ 1m	RF amplifier output pin.

Pin No.	Symbol	I/O	Equivalent circuit	Description
16	RF I	I	147	The RF amplifier output RFO is input with its capacitance coupled.
17	RFTC		147 147 50µ 50µ 10µ 10µ	External time-constant pin for RF level control.
18	AGCCONT	I	147	RF level control ON (limit level of 50%/30%)/OFF switching pin. OFF for Vcc, 30% for open or Vc and 50% for VEE.
19	LD_ON	I	147 19 VREF	APC amplifier ON/OFF switching pin. OFF for Vcc and ON for VEE.
20	Vcc		20 > Vcc	Vcc pin.

Electrical Characteristics

(Ta = 25°C, Vcc = 1.75V, VEE = -1.75V, VC = GND)

Unit		шA	ШA	مر ۲	dВ	В	>	>	۲ ا	В	В	ц	>	>	کر سر	В	В	В	>	>	مر ۲	۲ ۲	_ N	۲ سر
		13.23 n	-6.37 n	60.0 n	22.7 0		1	-1.25	120.0 n	22.4 0	22.4 0	3.0	-1.25		50 n	13.3 0	13.3 c	3.0 0	 	-1.25	170 n	1470 n	-	100 n
Max								- -	12(с.	- -		2			3.		- -			- 0	10
TVD	ч <i>к</i> .	9.8	-9.8 -	-10	19.7				0	19.4	19.4	0			0	10.3	10.3	0			-330	970	1590	
Min		6.37	-13.23	-50.0	16.7	ကို	1.45		-120.0	16.4	16.4	-3.0		1.25	-50	7.3	7.3	-3.0	1.25		-830	470	1400	-600
waveform	t method			Output DC measurement	Output AC measurement	Output AC measurement	Output DC measurement	Output DC measurement	Output DC measurement	Output AC measurement	Output AC measurement		Output DC measurement	Output DC measurement	Output DC measurement	Output AC measurement	Output AC measurement		Output DC measurement	Output DC measurement	Output DC measurement	Output DC measurement	Output DC measurement	Output DC measurement
	and measurement method	Input GND	Input GND	Input resistance $33k\Omega$	Input 1kHz 120mVp-p	Input 3MHz 120mVpp			Input resistance 33k0	Input 1kHz 120mVp-p	Input 1kHz 120mVp-p	V13-4 = V13-2 - V13-3			Input resistance 390kΩ	Input 1kHz 240mVp-p	Input 1kHz 240mVp-p	V11-4 = V11-2 - V11-3					LD OFF	
t biu snie-	nen Mea	20	9	15	15	15	15	15	13	13	13	13	13	13	7	7	1	11	-	7	2	2	2	2
	E4																				2.0V	2.0V	0.5V	2.0V
	E3																				2.7V	2.7V	2.7V	2.7V
ditions	E2																							
Bias conditions	Ē						300mV	300mV					300mV	300mV					5	5				
	12																				450µA	570µA	ОµА	ОμΑ
	1																							0.8mA
-	8	•	_																					
suc	6 7	0	0				0	0					0	0					0	0				
SW conditions	5																0			0				
	4															0			0					
N N	2 3				0 0		0 0	0 0		0	0		0	0										
	-				5																			0
Svmbol	0,000	lcc	E	V15-1	V15-2	V15-3	V15-4	V15-5	V13-1	V13-2	V13-3	V13-4	V13-5	V13-6	V11-1	V11-2	V11-3	V11-4	V11-5	V11-6	V2-1	V2-2	V2-3	V2-5
Measurement item		Current	consumption	Offset voltage 1	Voltage gain	Erequency response	Maximum output amplitude H	Maximum output amplitude L	Offset voltage	Voltage gain 1	Voltage gain 2	ង Voltage gain LL difference	Maximum output amplitude L	Maximum output amplitude H	Offset voltage 1	Voltage gain 1	Voltage gain 2	କଳ Voltage gain TE difference	Maximum output amplitude H	Maximum output amplitude L	Output voltage 1	Output voltage 2	Output voltage 3	Maximum output amplitude
No.		1	2	e	4	2	6	2	8	ი	10	7	12	13	14	15	16	17	18	19	20	5	22	23
									~			-	-	-	-			~			~~~	(1	()	(1)

į		> m	> u	> u	> u	>	>	>	۲ سر	ate.
	5 ;					 				F sté
Nax		-10	-20	1900	1700		2.2	0.5	100	е О
Tvn Max Llnit		-1900 -1322 -100	-1700 -1163 -200	1471	1204					ents th
Min		-1900	-1700	700	700	2.7	1.3		-100	sprese
) waveform	form			rol OFF	rol OFF				Output DC measurement	conditions 7 re
Description of I/O waveform	and measurement method	Level control: 50% – Level control OFF	Level control: 30% – Level control OFF	Level control: -50% – Level control OFF	Level control: -30% – Level control OFF					Note) O in the SW conditions 7 represents the OFF state.
t biu snie-	men Mea	2	2	2	7	18	18	18	10	ž
	E4	2.0V	2.0V	2.0V	2.0V					
	E3	0.5V/ 2.7V	1.3V/ 2.7V	0.5V/ 2.7V	2.2V/ 2.7V					
Iditions	E2			800mV 0.5V/ 2.7V	800mV 2.7V					
Bias conditions	E1	50mV	50mV							
	12	800µA 50mV	700µA 50mV	230µA	320µA					
	11									
	8			0	0					
s	7								0	
ition	9			0	0					
ouc	4 5									
SW conditions	3	0	0							
	2	0 0	0							
	1									
Sumhol		V2-7	V2-8	V2-9	V2-10	V18-1	V18-2	V18-3	V10-1	
NO. Measurement item Symbol		50% limit	30% limit	-50% limit	30% limit	High Level	Middle Level	Low Level	Center output voltage V10-1	
	2	RF level control						₽Ø		
Z		24	25	26	27	28	29	30	31	



Description of Functions

RF Amplifier

The photodiode current input to the input pins (PD1, PD2) are current-to-voltage (I-V) converted by the equivalent resistance of $58k\Omega$ at PD I-V amplifiers, respectively. The signal is added by the RF summing amplifier and then the I-V converted output voltage of the photodiode (A + B + C + D) is output to RFO pin. This pin is used check the eye pattern.



The frequency response of the RF output signal can be equalized by adding the capacitance (Cp) to RFI pin. The low frequency component of the RFO output voltage is as follows;

$$V_{RFO} = -2.75 \times (V_A + V_B)$$
$$= 159.5 k\Omega \times (iPD1 + iPD2)$$

Focus Error Amplifier

The difference between the RF I-V amplifier output VA and VB is obtained and the I-V converted voltage of the photodiode (A + C - B - D) is output.



The FE output voltage (low frequency) is as follows;

$$\label{eq:VFE} \begin{split} \mathsf{V}_{\mathsf{FE}} &= 5.4 \times (\mathsf{V}_{\mathsf{A}} - \mathsf{V}_{\mathsf{B}}) \\ &= (\mathsf{i}\mathsf{P}\mathsf{D}2 - \mathsf{i}\mathsf{P}\mathsf{D}1) \times 315 \mathsf{k}\Omega \end{split}$$

-9-

Tracking Error Amplifier

Each signal current from the photodiodes E and F is I-V converted and input to Pins 7 and 8 via a resistor which determines the gain. The signal is amplified by the gain amplifier, operated by the tracking error amplifier and then the (F-E) signal is output to Pin 11.



The balance adjustment is performed by varying the combined resistance value of the feedback resistors, which are T type-configured at the E I-V amplifier, by using the external resistance value of EI pin.

F I-V amplifier feedback resistance value = $R_{F1} + R_{F2} + \frac{R_{F1} \times R_{F2}}{R_{F3}} = 403 k\Omega$

E I-V amplifier feedback resistance value = (Re1 // R1) + Re2 + $\frac{(Re1 // R1) \times Re2}{(Re3 // R2)}$

Leave EI pin open when the balance adjustment is not executed in this IC. The gain for F I-V and E I-V amplifiers becomes the same when EI pin is left open.

Center Voltage Generation Circuit

This circuit provides the center potential when this IC is used at single power supply. The maximum current is approximately ± 3 mA. The output impedance is approximately 50Ω .



APC & Laser Power Control



• APC

When the laser diode is driven by a constant current, the optical power output has extremely large negative temperature characteristics. The APC circuit is used to maintain the optical power output at a constant level. The laser diode current is controlled according to the monitor photo diode output.

APC is set to ON by connecting the LD_ON pin to Vcc; OFF by connecting it to Vcc.

Application Circuit

• For single power supply +3.5V



• For dual power supply ±1.75V



Application circuits shown are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits or for any infringement of third party patent and other right due to same.

• LASER POWER CONTROL (LPC)

The RF level is stabilized by attaching an offset to the APC V_L and controlling the laser power in sync with the RF level fluctuations.

The RF O and RF I levels are compared and the larger of the two is smoothed by the RFTC's external CR.

This signal is then compared with the reference level.

The laser power is controlled by attaching an offset to V_L according to the results of comparison with the reference level.

Set the reference level to 670mV. (center voltage reference)

When the reference level is changed, connect the external resistor to the AGCVTH pin (Pin 1). The reference level can be lowered by connecting the resistor between Pin 1 and the center output voltage or between Pin 20 and Vcc.

The AGCCONT pin (pin 18) is used to switch the level of the laser power control circuit; OFF, ON (laser power limit of 30%) and ON (laser power limit of 50%)

AGCCONT	LPC	LPC limit	V∟ variable range
H (Vcc)	OFF	—	Approximately 1.27V
M (VC or OPEN)	ON	30%	Approximately 1.27V ± 350mV
L (VEE)	ON	50%	Approximately 1.27V ± 570mV

Note) For the laser power limit, 50% is recommended for PD IC; 30% for LC.

Notes on Operation

1. Power supply

The CXA2550M/N can be used either at dual power supply or single power supply. The table below shows the connection of power supply for each case.

	Vcc	Vee	VC
Dual power supply	+power supply	-power supply	GND
Single power supply	Power supply	GND	OPEN

2. RF amplifier

In this circuit, the IC internal phase compensation value is set so as to support the voltage output-type pickup. Therefore, when the current output-type pickup is used, the capacitance of optical pickup and leads etc. are attached to PD1 and PD2 pins and oscillation may occur.

3. laser power control

The RF level is stabilized by attaching an offset to the APC V_L and controlling the laser power in sync with the RF level fluctuations. Therefore, use this circuit in the state where the focus servo is applied.

The laser life is shortened by increasing the laser power when the less light is reflected from the disc. It is recommended that the typical laser power value is set lower to maintain the laser life.

Take care of the laser maximum ratings when using the laser power control circuit.

Package Outline Unit: mm

CXA2550M

20PIN SOP (PLASTIC) 300mil





PACKAGE STRUCTURE

	PACKAGE MATERIAL	EPOXY / PHENOL RESIN
SONY CODE SOP-20P-L01	LEAD TREATMENT	SOLDER PLATING
EIAJ CODE *SOP020-P-0300-A	LEAD MATERIAL	COPPER ALLOY
JEDEC CODE	PACKAGE WEIGHT	0.3g

CXA2550N

20PIN SSOP (PLASTIC)







NOTE: Dimension "*" does not include mold protrusion.

	PACKAGE STRUCTURE								
			PACKAGE MATERIAL	EPOXY RESIN					
SONY CODE	SSOP-20P-L01		LEAD TREATMENT	SOLDER / PALLADIUM PLATING					
EIAJ CODE	SSOP020-P-0044		LEAD MATERIAL	COPPER / 42 ALLOY					
JEDEC CODE			PACKAGE WEIGHT	0.1g					